

V _{DS} (V)	R _{DS(on)} (mΩ)	I _D (A)
30	36 @ V _{GS} = 10V	5.9
	53 @ V _{GS} = 4.5V	4.9

Features

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

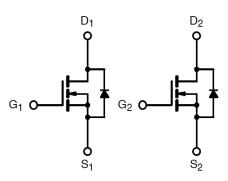
Application

- High-Side DC/DC Conversion
- Notebook
- Sever

Ordering Information

Part No.	Package	Packing		
TSM4936DCS RL	SOP-8	2.5Kpcs / 13" Reel		

Block Diagram



Dual N-Channel MOSFET

Absolute Maximum Rating (Ta = 25°C unless otherwise noted)

Parameter		Limit	Unit		
	V _{DS}	30	V		
	V _{GS}	±20	V		
	Ι _D	5.9	А		
Pulsed Drain Current		40	А		
Continuous Source Current (Diode Conduction) ^{a,b}		1.0	А		
Ta = 25°C	- P _D	3.0	W		
Ta = 75°C		2.1	VV		
Operating Junction Temperature		+150	°C		
Operating Junction and Storage Temperature Range		- 55 to +150	°C		
	Ta = 25°C Ta = 75°C		$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$		

Thermal Performance

Symbol	Limit	Unit
Rθ _{JF}	32	°C/W
Rθ _{JA}	50	°C/W
	Rθ _{JF}	R Θ_{JF} 32

Notes:

a. Pulse width limited by the Maximum junction temperature

b. Surface Mounted on FR4 Board, t \leq 10 sec.



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TSM4936D 30V N-Channel MOSFET

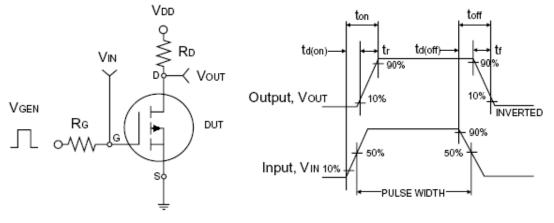
Electrical Specifications

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_{D} = 250uA$	BV _{DSS}	30			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	V _{GS(TH)}	1	1.4	3	V
Gate Body Leakage	V_{GS} = ±20V, V_{DS} = 0V	I _{GSS}			±100	nA
Zero Gate Voltage Drain Current	V_{DS} = 24V, V_{GS} = 0V	I _{DSS}			1.0	μA
On-State Drain Current ^a	V _{DS} ≥ 5V, V _{GS} = 10V	I _{D(ON)}	30			А
Drain Course On State Desistence ^a	in-Source On-State Resistance ^a $\frac{V_{GS} = 10V, I_D = 5.9A}{V_{GS} = 4.5V, I_D = 4.9A} R_{DS(ON)}$		32	36	mΩ	
Drain-Source On-State Resistance			42	53		
Forward Transconductance ^a	V _{DS} = 15V, I _D = 5.9A	g _{fs}		15		S
Diode Forward Voltage	I _S = 1A, V _{GS} = 0V	V _{SD}		0.76	1.0	V
Dynamic ^ь						
Total Gate Charge		Qg	-	13		
Gate-Source Charge	V _{DS} = 15V, I _D = 5.9A, V _{GS} = 10V	Q _{gs}		4.2		nC
Gate-Drain Charge		Q _{gd}		3.1		
Input Capacitance	$V_{DS} = 15V, V_{GS} = 0V,$	C _{iss}		610		
Output Capacitance		C _{oss}		100		pF
Reverse Transfer Capacitance	f = 1.0MHz	C _{rss}		77		
Switching ^c	•	·				
Turn-On Delay Time	- V _{DD} = 15V, R _L = 15Ω, I _D = 1A, V _{GEN} = 10V,	t _{d(on)}		9.1		
Turn-On Rise Time		t _r		16.5		
Turn-Off Delay Time		t _{d(off)}		23		nS
Turn-Off Fall Time	$R_{G} = 6\Omega$	t _f		3.5		

Notes:

a. pulse test: PW \leq 300µS, duty cycle \leq 2% b. For DESIGN AID ONLY, not subject to production testing.

b. Switching time is essentially independent of operating temperature.



Switching Test Circuit

Switchin Waveforms



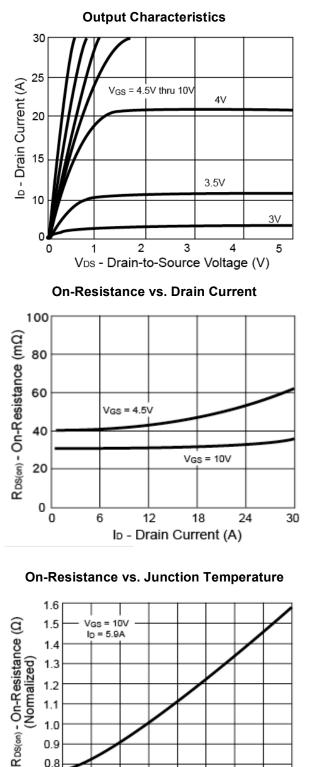
1.1 1.0

0.9 0.8 0.6

> -50 -25

TSM4936D 30V N-Channel MOSFET

Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)



25

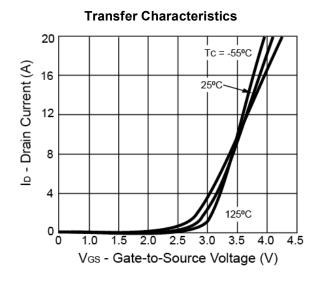
50

Tj - Junction Temperature (°C)

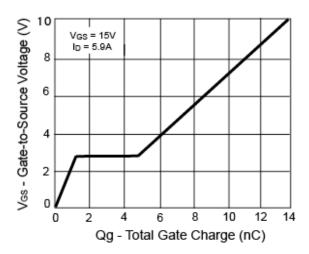
75

100

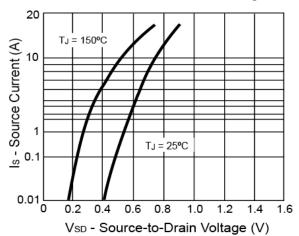
0



Gate Charge



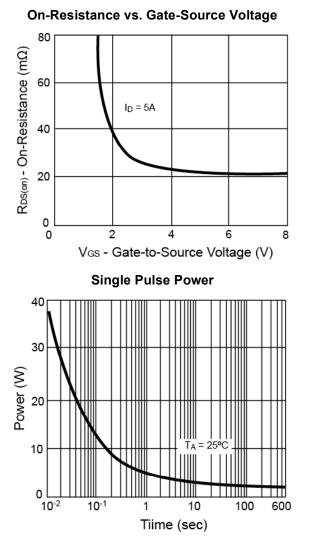
Source-Drain Diode Forward Voltage

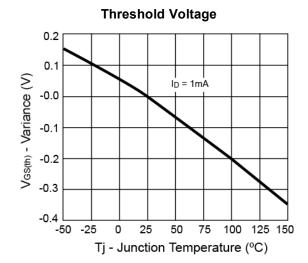


125 150

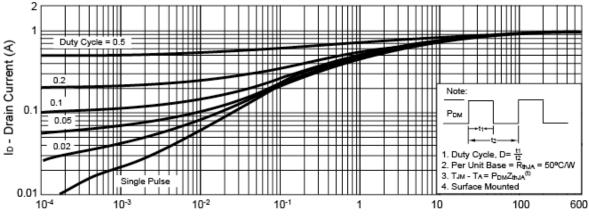


Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)





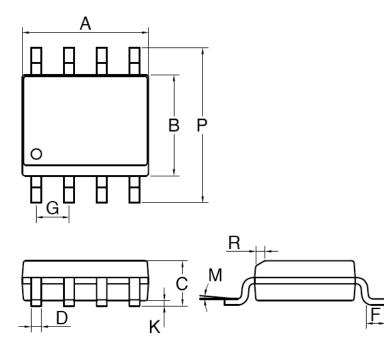
Normalized Thermal Transient Impedance, Junction-to-Ambient



Square Wave Pulse Duration (sec)

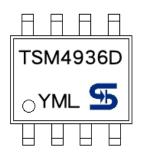


SOP-8 Mechanical Drawing



SOP-8 DIMENSION					
DIM	MILLIMETERS		INCHES		
	MIN	MAX	MIN	MAX.	
Α	4.80	5.00	0.189	0.196	
В	3.80	4.00	0.150	0.157	
С	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27	BSC	0.05BSC		
K	0.10	0.25	0.004	0.009	
М	0°	7°	0°	7°	
Р	5.80	6.20	0.229	0.244	
R	0.25	0.50	0.010	0.019	

Marking Diagram



- Y = Year Code
- M = Month Code

(A=Jan, B=Feb, C=Mar, D=Apl, E=May, F=Jun, G=Jul, H=Aug, I=Sep, J=Oct, K=Nov, L=Dec)

L = Lot Code



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